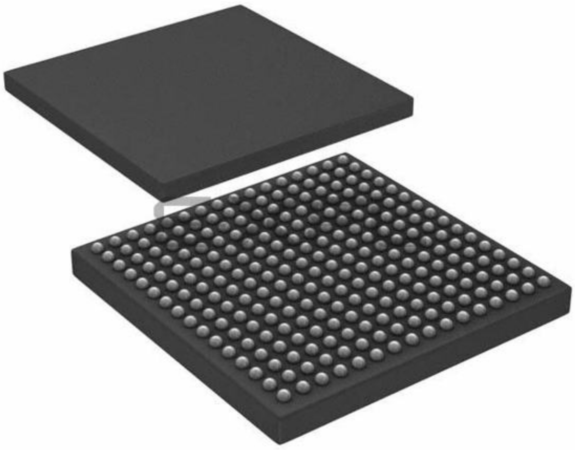
Microchip Technology - A2F200M3F-1FGG256I Datasheet



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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

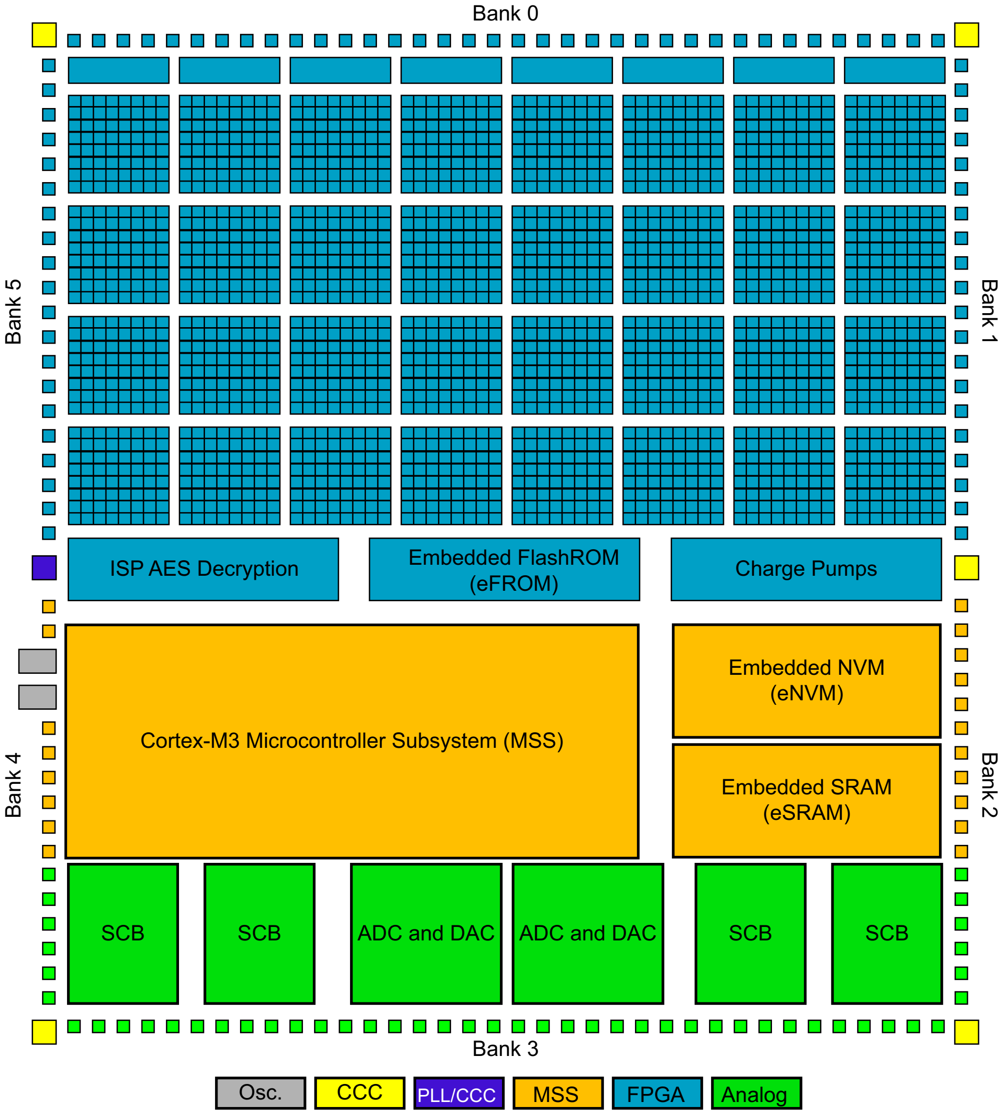
What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	256KB
RAM Size	64KB
Peripherals	DMA, POR, WDT
Connectivity	EBI/EMI, Ethernet, I²C, SPI, UART/USART
Speed	100MHz
Primary Attributes	ProASIC®3 FPGA, 200K Gates, 4608 D-Flip-Flops
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a2f200m3f-1fgg256i

Email: info@E-XFL.COM Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

SmartFusion cSoC System Architecture



Note: Architecture for A2F200

1 – SmartFusion Family Overview

Introduction

The SmartFusion® family of cSoCs builds on the technology first introduced with the Fusion mixed signal FPGAs. SmartFusion cSoCs are made possible by integrating FPGA technology with programmable high-performance analog and hardened ARM Cortex-M3 microcontroller blocks on a flash semiconductor process. The SmartFusion cSoC takes its name from the fact that these three discrete technologies are integrated on a single chip, enabling the lowest cost of ownership and smallest footprint solution to you.

General Description

Microcontroller Subsystem (MSS)

The MSS is composed of a 100 MHz Cortex-M3 processor and integrated peripherals, which are interconnected via a multi-layer AHB bus matrix (ABM). This matrix allows the Cortex-M3 processor, FPGA fabric master, Ethernet media access controller (MAC), when available, and peripheral DMA (PDMA) controller to act as masters to the integrated peripherals, FPGA fabric, embedded nonvolatile memory (eNVM), embedded synchronous RAM (eSRAM), external memory controller (EMC), and analog compute engine (ACE) blocks.

SmartFusion cSoCs of different densities offer various sets of integrated peripherals. Available peripherals include SPI, I^2C, and UART serial ports, embedded FlashROM (EFROM), 10/100 Ethernet MAC, timers, phase-locked loops (PLLs), oscillators, real-time counters (RTC), and peripheral DMA controller (PDMA).

Programmable Analog

Analog Front-End (AFE)

SmartFusion cSoCs offer an enhanced analog front-end compared to Fusion devices. The successive approximation register analog-to-digital converters (SAR ADC) are similar to those found on Fusion devices. SmartFusion cSoC also adds first order sigma-delta digital-to-analog converters (SDD DAC).

SmartFusion cSoCs can handle multiple analog signals simultaneously with its signal conditioning blocks (SCBs). SCBs are made of a combination of active bipolar prescalers (ABPS), comparators, current monitors and temperature monitors. ABPS modules allow larger bipolar voltages to be fed to the ADC. Current monitors take the voltage across an external sense resistor and convert it to a voltage suitable for the ADC input range. Similarly, the temperature monitor reads the current through an external PN-junction (diode or transistor) and converts it internally for the ADC. The SCB also includes comparators to monitor fast signal thresholds without using the ADC. The output of the comparators can be fed to the analog compute engine or the ADC.

Analog Compute Engine (ACE)

The mixed signal blocks found in SmartFusion cSoCs are controlled and connected to the rest of the system via a dedicated processor called the analog compute engine (ACE). The role of the ACE is to offload control of the analog blocks from the Cortex-M3, thus offering faster throughput or better power consumption compared to a system where the main processor is in charge of monitoring the analog resources. The ACE is built to handle sampling, sequencing, and post-processing of the ADCs, DACs, and SCBs.

This enables reduction or complete removal of expensive voltage monitor and brownout detection devices from the PCB design. Flash-based SmartFusion cSoCs simplify total system design and reduce cost and design risk, while increasing system reliability.

Immunity to Firm Errors

Firm errors occur most commonly when high-energy neutrons, generated in the atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O configuration behavior in an unpredictable way.

Another source of radiation-induced firm errors is alpha particles. For alpha radiation to cause a soft or firm error, its source must be in very close proximity to the affected circuit. The alpha source must be in the package molding compound or in the die itself. While low-alpha molding compounds are being used increasingly, this helps reduce but does not entirely eliminate alpha-induced firm errors.

Firm errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not occur in SmartFusion cSoCs. Once it is programmed, the flash cell configuration element of SmartFusion cSoCs cannot be altered by high energy neutrons and is therefore immune to errors from them. Recoverable (or soft) errors occur in the user data SRAMs of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the *FlashPro User’s Guide* for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

The I/Os are controlled by the JTAG Boundary Scan register during programming, except for the analog pins (AC, AT and AV). The Boundary Scan register of the AG pin can be used to enable/disable the gate driver in software v9.0.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify (Figure 1-1 on page 1-4).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:

   1 – I/O is set to drive out logic High

   0 – I/O is set to drive out logic Low

   Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming

   Z -Tri-State: I/O is tristated

Theta-JA

Junction-to-ambient thermal resistance (θ_{JA}) is determined under standard conditions specified by JEDEC (JESD-51), but it has little relevance in actual performance of the product. It should be used with caution but is useful for comparing the thermal performance of one package to another.

A sample calculation showing the maximum power dissipation allowed for the A2F200-FG484 package under forced convection of 1.0 m/s and 75°C ambient temperature is as follows:

$$\text{Maximum Power Allowed} = \frac{T_{J(MAX)} - T_{A(MAX)}}{\theta_{JA}}$$

EQ 4

where

θ_{JA} = 19.00°C/W (taken from Table 2-6 on page 2-7).

T_A = 75.00°C

$$\text{Maximum Power Allowed} = \frac{100.00°C - 75.00°C}{19.00°C/W} = 1.3\ W$$

EQ 5

The power consumption of a device can be calculated using the Microsemi SoC Products Group power calculator. The device's power consumption must be lower than the calculated maximum power dissipation by the package. If the power consumption is higher than the device's maximum allowable power dissipation, a heat sink can be attached on top of the case, or the airflow inside the system must be increased.

Theta-JB

Junction-to-board thermal resistance (θ_{JB}) measures the ability of the package to dissipate heat from the surface of the chip to the PCB. As defined by the JEDEC (JESD-51) standard, the thermal resistance from junction to board uses an isothermal ring cold plate zone concept. The ring cold plate is simply a means to generate an isothermal boundary condition at the perimeter. The cold plate is mounted on a JEDEC standard board with a minimum distance of 5.0 mm away from the package edge.

Theta-JC

Junction-to-case thermal resistance (θ_{JC}) measures the ability of a device to dissipate heat from the surface of the chip to the top or bottom surface of the package. It is applicable for packages used with external heat sinks. Constant temperature is applied to the surface in consideration and acts as a boundary condition. This only applies to situations where all or nearly all of the heat is dissipated through the surface in consideration.

Calculation for Heat Sink

For example, in a design implemented in an A2F200-FG484 package with 2.5 m/s airflow, the power consumption value using the power calculator is 3.00 W. The user-dependent T_a and T_j are given as follows:

T_J = 100.00°C

T_A = 70.00°C

From the datasheet:

θ_{JA} = 17.00°C/W

θ_{JC} = 8.28°C/W

$$P = \frac{T_J - T_A}{\theta_{JA}} = \frac{100°C - 70°C}{17.00\ W} = 1.76\ W$$

EQ 6

The 1.76 W power is less than the required 3.00 W. The design therefore requires a heat sink, or the airflow where the device is mounted should be increased. The design's total junction-to-air thermal resistance requirement can be estimated by EQ 7:

$$\theta_{JA(total)} = \frac{T_J - T_A}{P} = \frac{100°C - 70°C}{3.00\ W} = 10.00°C/W$$

EQ 7

Determining the heat sink's thermal performance proceeds as follows:

$$\theta_{JA(TOTAL)} = \theta_{JC} + \theta_{CS} + \theta_{SA}$$

EQ 8

where

θ_{JA} = 0.37°C/W

= Thermal resistance of the interface material between the case and the heat sink, usually provided by the thermal interface manufacturer

θ_{SA} = Thermal resistance of the heat sink in °C/W

$$\theta_{SA} = \theta_{JA(TOTAL)} - \theta_{JC} - \theta_{CS}$$

EQ 9

$$\theta_{SA} = 13.33°C/W - 8.28°C/W - 0.37°C/W = 5.01°C/W$$

A heat sink with a thermal resistance of 5.01°C/W or better should be used. Thermal resistance of heat sinks is a function of airflow. The heat sink performance can be significantly improved with increased airflow.

Carefully estimating thermal resistance is important in the long-term reliability of an FPGA. Design engineers should always correlate the power consumption of the device with the maximum allowable power dissipation of the package selected for that device.

Note: The junction-to-air and junction-to-board thermal resistances are based on JEDEC standard (JESD-51) and assumptions made in building the model. It may not be realized in actual application and therefore should be used with a degree of caution. Junction-to-case thermal resistance assumes that all power is dissipated through the case.

Temperature and Voltage Derating Factors

Table 2-7 • **Temperature and Voltage Derating Factors for Timing Delays (normalized to T_J = 85°C, worst-case VCC = 1.425 V)**

Array Voltage VCC (V)	**Junction Temperature (°C)**					
	–40°C	**0°C**	**25°C**	**70°C**	**85°C**	**100°C**
1.425	0.86	0.91	0.93	0.98	1.00	1.02
1.500	0.81	0.86	0.88	0.93	0.95	0.96
1.575	0.78	0.83	0.85	0.90	0.91	0.93

Table 2-14 • **Different Components Contributing to Dynamic Power Consumption in SmartFusion cSoCs**

Parameter	Definition	Power Supply		Device			Units
		Name	Domain	A2F060	A2F200	A2F500	
PAC24	Current Monitor Power Contribution	See Table 2-93 on page 2-78	–	1.03			mW
PAC25	ABPS Power Contribution	See Table 2-96 on page 2-82	–	0.70			mW
PAC26	Sigma-Delta DAC Power Contribution[2]	See Table 2-98 on page 2-85	–	0.58			mW
PAC27	Comparator Power Contribution	See Table 2-97 on page 2-84	–	1.02			mW
PAC28	Voltage Regulator Power Contribution[3]	See Table 2-99 on page 2-87	–	36.30			mW

Notes:

1. *For a different use of MSS peripherals and resources, refer to SmartPower.*
2. *Assumes Input = Half Scale Operation mode.*
3. *Assumes 100 mA load on 1.5 V domain.*

Table 2-15 • **Different Components Contributing to the Static Power Consumption in SmartFusion cSoCs**

Parameter	Definition	Power Supply		Device			Units
		Name	Domain	A2F060	A2F200	A2F200	
PDC1	Core static power contribution in SoC mode	VCC	1.5 V	11.10	23.70	37.95	mW
PDC2	Device static power contribution in Standby Mode	See Table 2-8 on page 2-10	–	11.10	23.70	37.95	mW
PDC3	Device static power contribution in Time Keeping mode	See Table 2-8 on page 2-10	3.3 V	33.00	33.00	33.00	µW
PDC7	Static contribution per input pin (standard dependent contribution)	VCCxxxxIOBx/VCC	See Table 2-10 and Table 2-11 on page 2-11.				
PDC8	Static contribution per output pin (standard dependent contribution)	VCCxxxxIOBx/VCC	See Table 2-12 and Table 2-13 on page 2-11.				
PDC9	Static contribution per PLL	VCC	1.5 V	2.55	2.55	2.55	mW

Table 2-16 • **eNVM Dynamic Power Consumption**

Parameter	Description	Condition	Min.	Typ.	Max.	Units
eNVM System	eNVM array operating power	Idle		795		µA
		Read operation	See Table 2-14 on page 2-12.			
		Erase		900		µA
		Write		900		µA
PNVMCTRL	eNVM controller operating power			20		µW/MHz

Standby Mode

$P_{DYN} = P_{RC\text{-}OSC} + P_{LPXTAL\text{-}OSC}$

Time Keeping Mode

$P_{DYN} = P_{LPXTAL\text{-}OSC}$

Global Clock Dynamic Contribution—P_{CLOCK}

SoC Mode

$P_{CLOCK} = (P_{AC1} + N_{SPINE} * P_{AC2} + N_{ROW} * PAC3 + N_{S\text{-}CELL} * P_{AC4}) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Device Architecture" chapter of the *SmartFusion FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Device Architecture" chapter of the *SmartFusion FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

Standby Mode and Time Keeping Mode

$P_{CLOCK} = 0$ W

Sequential Cells Dynamic Contribution—$P_{S\text{-}CELL}$

SoC Mode

$P_{S\text{-}CELL} = N_{S\text{-}CELL} * (P_{AC5} + (\alpha_1 / 2) * P_{AC6}) * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-17 on page 2-18.

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

$P_{S\text{-}CELL} = 0$ W

Combinatorial Cells Dynamic Contribution—$P_{C\text{-}CELL}$

SoC Mode

$P_{C\text{-}CELL} = N_{C\text{-}CELL} * (\alpha_1 / 2) * P_{AC7} * F_{CLK}$

$N_{C\text{-}CELL}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-17 on page 2-18.

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

$P_{C\text{-}CELL} = 0$ W

Routing Net Dynamic Contribution—P_{NET}

SoC Mode

$P_{NET} = (N_{S\text{-}CELL} + N_{C\text{-}CELL}) * (\alpha_1 / 2) * P_{AC8} * F_{CLK}$

$N_{S\text{-}CELL}$ is the number VersaTiles used as sequential modules in the design.

$N_{C\text{-}CELL}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-17 on page 2-18.

F_{CLK} is the frequency of the clock driving the logic including these nets.

Microcontroller Subsystem Dynamic Contribution—P_{MSS}

SoC Mode

$P_{MSS} = P_{AC22}$

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that the net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100%, as all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
  - Bit 0 (LSB) = 100%
  - Bit 1 = 50%
  - Bit 2 = 25%
  - …
  - Bit 7 (MSB) = 0.78125%
  - Average toggle rate = (100% + 50% + 25% + 12.5% + . . . 0.78125%) / 8.

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When non-tristate output buffers are used, the enable rate should be 100%.

Table 2-17 • **Toggle Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

Table 2-18 • **Enable Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
β_1	I/O output buffer enable rate	Toggle rate of the logic driving the output buffer
β_2	FPGA fabric SRAM enable rate for read operations	12.5%
β_3	FPGA fabric SRAM enable rate for write operations	12.5%
β_4	eNVM enable rate for read operations	< 5%

Timing Characteristics

Table 2-50 • **1.8 V LVCMOS High Slew**
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 1.7 V
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.60	11.06	0.04	1.14	0.39	8.61	11.06	2.61	1.59	10.67	13.12	ns
	–1	0.50	9.22	0.03	0.95	0.32	7.17	9.22	2.18	1.33	8.89	10.93	ns
4 mA	Std.	0.60	6.46	0.04	1.14	0.39	5.53	6.46	3.04	2.66	7.59	8.51	ns
	–1	0.50	5.38	0.03	0.95	0.32	4.61	5.38	2.54	2.22	6.33	7.10	ns
6 mA	Std.	0.60	4.16	0.04	1.14	0.39	3.99	4.16	3.34	3.18	6.05	6.22	ns
	–1	0.50	3.47	0.03	0.95	0.32	3.32	3.47	2.78	2.65	5.04	5.18	ns
8 mA	Std.	0.60	3.69	0.04	1.14	0.39	3.76	3.67	3.40	3.31	5.81	5.73	ns
	–1	0.50	3.07	0.03	0.95	0.32	3.13	3.06	2.84	2.76	4.85	4.78	ns
12 mA	Std.	0.60	3.38	0.04	1.14	0.39	3.44	2.86	3.50	3.82	5.50	4.91	ns
	–1	0.50	2.81	0.03	0.95	0.32	2.87	2.38	2.92	3.18	4.58	4.10	ns
16 mA	Std.	0.60	3.38	0.04	1.14	0.39	3.44	2.86	3.50	3.82	5.50	4.91	ns
	–1	0.50	2.81	0.03	0.95	0.32	2.87	2.38	2.92	3.18	4.58	4.10	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

Table 2-51 • **1.8 V LVCMOS Low Slew**
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 1.7 V
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.60	14.24	0.04	1.14	0.39	13.47	14.24	2.62	1.54	15.53	16.30	ns
	–1	0.50	11.87	0.03	0.95	0.32	11.23	11.87	2.18	1.28	12.94	13.59	ns
4 mA	Std.	0.60	9.74	0.04	1.14	0.39	9.92	9.62	3.05	2.57	11.98	11.68	ns
	–1	0.50	8.11	0.03	0.95	0.32	8.26	8.02	2.54	2.14	9.98	9.74	ns
6 mA	Std.	0.60	7.67	0.04	1.14	0.39	7.81	7.24	3.34	3.08	9.87	9.30	ns
	–1	0.50	6.39	0.03	0.95	0.32	6.51	6.03	2.79	2.56	8.23	7.75	ns
8 mA	Std.	0.60	7.15	0.04	1.14	0.39	7.29	6.75	3.41	3.21	9.34	8.80	ns
	–1	0.50	5.96	0.03	0.95	0.32	6.07	5.62	2.84	2.68	7.79	7.34	ns
12 mA	Std.	0.60	6.76	0.04	1.14	0.39	6.89	6.75	3.50	3.70	8.95	8.81	ns
	–1	0.50	5.64	0.03	0.95	0.32	5.74	5.62	2.92	3.08	7.46	7.34	ns
16 mA	Std.	0.60	6.76	0.04	1.14	0.39	6.89	6.75	3.50	3.70	8.95	8.81	ns
	–1	0.50	5.64	0.03	0.95	0.32	5.74	5.62	2.92	3.08	7.46	7.34	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

Table 2-52 • **1.8 V LVCMOS High Slew**
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 1.7 V
Applicable to MSS I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	Std.	0.22	2.77	0.09	1.09	1.64	0.22	2.82	2.72	2.21	2.25	ns
	–1	0.18	2.31	0.07	0.91	1.37	0.18	2.35	2.27	1.84	1.87	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-53 • **Minimum and Maximum DC Input and Output Levels Applicable to FPGA I/O Banks**

1.5 V LVCMOS	**VIL**		**VIH**		**VOL**	**VOH**	**I_{OL}**	**I_{OH}**	**I_{OSL}**	**I_{OSH}**	**I_{IL}**	**I_{IH}**
Drive Strength	**Min. V**	**Max. V**	**Min. V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[1]**	**Max. mA[1]**	**µA[2]**	**µA[2]**
2 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.575	0.25* VCCxxxxIOBx	0.75 * VCCxxxxIOBx	2	2	16	13	15	15
4 mA	–0.3	0.35* VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.575	0.25* VCCxxxxIOBx	0.75 * VCCxxxxIOBx	4	4	33	25	15	15
6 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.575	0.25* VCCxxxxIOBx	0.75 * VCCxxxxIOBx	6	6	39	32	15	15
8 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.575	0.25* VCC	0.75 * VCCxxxxIOBx	8	8	55	66	15	15
12 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.575	0.25 * VCCxxxxIOBx	0.75 * VCCxxxxIOBx	12	12	55	66	15	15

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Software default selection highlighted in gray.*

Table 2-54 • **Minimum and Maximum DC Input and Output Levels Applicable to MSS I/O Banks**

1.5 V LVCMOS	**VIL**		**VIH**		**VOL**	**VOH**	**I_{OL}**	**I_{OH}**	**I_{OSL}**	**I_{OSH}**	**I_{IL}**	**I_{IH}**
Drive Strength	**Min. V**	**Max. V**	**Min. V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[1]**	**Max. mA[1]**	**µA[2]**	**µA[2]**
2 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.575	0.25 * VCCxxxxIOBx	0.75 * VCCxxxxIOBx	2	2	16	13	15	15

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Software default selection highlighted in gray.*

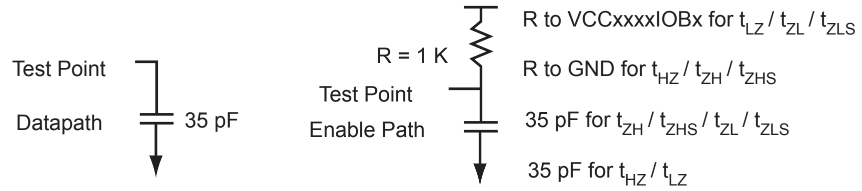


Figure 2-9 • **AC Loading**

Table 2-55 • **AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	**Input High (V)**	**Measuring Point* (V)**	**V_{REF} (typ.) (V)**	**C_{LOAD} (pF)**
0	1.5	0.75	–	35

* *Measuring point = $V_{trip.}$ See Table 2-22 on page 2-24 for a complete table of trip points.*

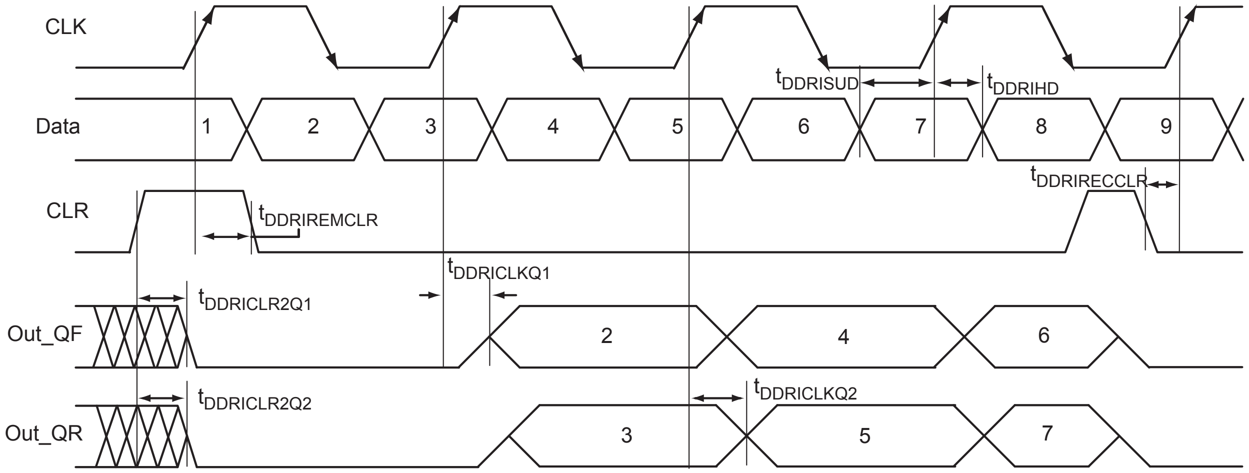


Figure 2-20 • **Input DDR Timing Diagram**

Timing Characteristics

Table 2-75 • **Input DDR Propagation Delays**
Worst Commercial-Case Conditions: T_J = 85°C, Worst Case VCC = 1.425 V

Parameter	Description	–1	Units
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR for Input DDR	0.39	ns
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF for Input DDR	0.28	ns
$t_{DDRISUD}$	Data Setup for Input DDR	0.29	ns
t_{DDRIHD}	Data Hold for Input DDR	0.00	ns
$t_{DDRICLR2Q1}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.58	ns
$t_{DDRICLR2Q2}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.47	ns
$t_{DDRIREMCLR}$	Asynchronous Clear Removal time for Input DDR	0.00	ns
$t_{DDRIRECCLR}$	Asynchronous Clear Recovery time for Input DDR	0.23	ns
$t_{DDRIWCLR}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.22	ns
$t_{DDRICKMPWH}$	Clock Minimum Pulse Width High for Input DDR	0.36	ns
$t_{DDRICKMPWL}$	Clock Minimum Pulse Width Low for Input DDR	0.32	ns
$F_{DDRIMAX}$	Maximum Frequency for Input DDR	350	MHz

Note: For derating values at specific junction temperature and voltage-supply levels, refer to Table 2-7 on page 2-9 for derating values.

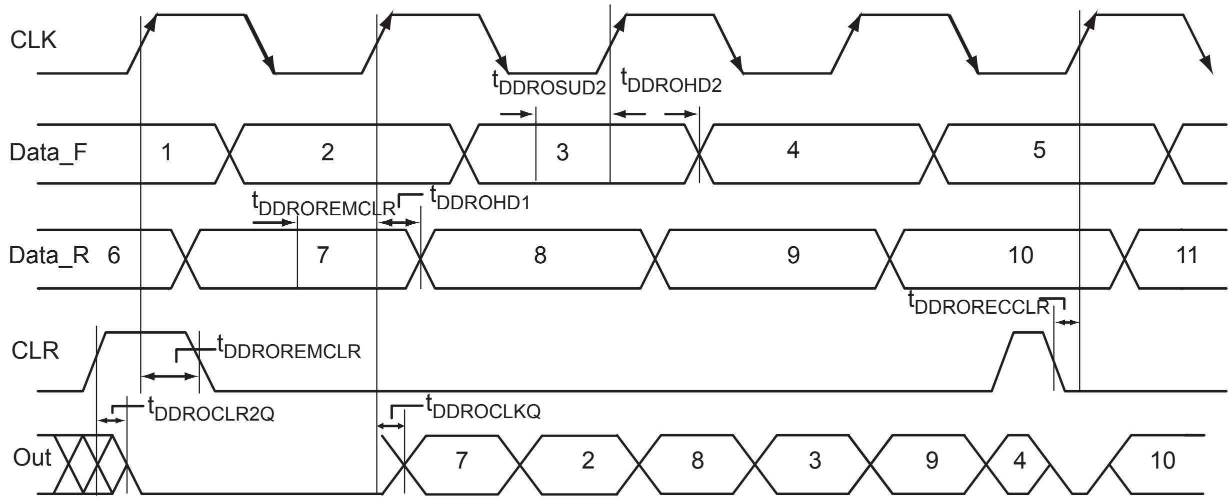


Figure 2-22 • **Output DDR Timing Diagram**

Timing Characteristics

Table 2-77 • **Output DDR Propagation Delays**
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Units
$t_{DDROCLKQ}$	Clock-to-Out of DDR for Output DDR	0.71	ns
$t_{DDROSUD1}$	Data_F Data Setup for Output DDR	0.38	ns
$t_{DDROSUD2}$	Data_R Data Setup for Output DDR	0.38	ns
$t_{DDROHD1}$	Data_F Data Hold for Output DDR	0.00	ns
$t_{DDROHD2}$	Data_R Data Hold for Output DDR	0.00	ns
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out for Output DDR	0.81	ns
$t_{DDROREMCLR}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{DDRORECCLR}$	Asynchronous Clear Recovery Time for Output DDR	0.23	ns
$t_{DDROWCLR1}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.22	ns
$t_{DDROCKMPWH}$	Clock Minimum Pulse Width High for the Output DDR	0.36	ns
$t_{DDROCKMPWL}$	Clock Minimum Pulse Width Low for the Output DDR	0.32	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	350	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

Main and Lower Power Crystal Oscillator

The tables below describes the electrical characteristics of the main and low power crystal oscillator.

Table 2-84 • **Electrical Characteristics of the Main Crystal Oscillator**

Parameter	Description	Condition	Min.	Typ.	Max.	Units
	Operating frequency	Using external crystal	0.032		20	MHz
		Using ceramic resonator	0.5		8	MHz
		Using RC Network	0.032		4	MHz
	Output duty cycle			50		%
	Output jitter	With 10 MHz crystal		1		ns RMS
IDYNXTAL	Operating current	RC		0.6		mA
		0.032–0.2		0.6		mA
		0.2–2.0		0.6		mA
		2.0–20.0		0.6		mA
ISTBXTAL	Standby current of crystal oscillator			10		µA
PSRRXTAL	Power supply noise tolerance			0.5		Vp-p
VIHXTAL	Input logic level High		90% of VCC			V
VILXTAL	Input logic level Low				10% of VCC	V
	Startup time	RC [Tested at 3.24Mhz]		300	550	µs
		0.032–0.2 [Tested at 32KHz]		500	3,000	µs
		0.2–2.0 [Tested at 2MHz]		8	12	µs
		2.0–20.0 [Tested at 20MHz]		160	180	µs

Table 2-85 • **Electrical Characteristics of the Low Power Oscillator**

Parameter	Description	Condition	Min.	Typ.	Max.	Units
	Operating frequency			32		KHz
	Output duty cycle			50		%
	Output jitter			30		ns RMS
IDYNXTAL	Operating current	32 KHz		10		µA
ISTBXTAL	Standby current of crystal oscillator			2		µA
PSRRXTAL	Power supply noise tolerance			0.5		Vp-p
VIHXTAL	Input logic level High		90% of VCC			V
VILXTAL	Input logic level Low				10% of VCC	V
	Startup time	Test load used: 20 pF		2.5		s
		Test load used: 30 pF		3.7	13	s

Temperature Monitor

Unless otherwise noted, temperature monitor performance is specified with a 2N3904 diode-connected bipolar transistor from National Semiconductor or Infineon Technologies, nominal power supply voltages, with the output measured using the internal voltage reference with the internal ADC in 12-bit mode and 62.5 Ksps. After digital compensation. Unless otherwise noted, the specifications pertain to conditions where the SmartFusion cSoC and the sensing diode are at the same temperature.

Table 2-94 • **Temperature Monitor Performance Specifications**

Specification	Test Conditions	Min.	Typical	Max.	Units
Input diode temperature range		–55		150	°C
		233.2		378.15	K
Temperature sensitivity			2.5		mV/K
Intercept	Extrapolated to 0K		0		V
Input referred temperature offset error	At 25°C (298.15K)		±1	1.5	°C
Gain error	Slope of BFSL vs. 2.5 mV/K		±1	2.5	% nom.
Overall accuracy	Peak error from ideal transfer function		±2	±3	°C
Input referred noise	At 25°C (298.15K) – no output averaging		4		°C rms
Output current	Idle mode		100		µA
	Final measurement phases		10		µA
Analog settling time	Measured to 0.1% of final value, (with ADC load)				
	From TM_STB (High)	5			µs
	From ADC_START (High)	5		105	µs
AT parasitic capacitance				500	pF
Power supply rejection ratio	DC (0–10 KHz)	1.2	0.7		°C/V
Input referred temperature sensitivity error	Variation due to device temperature (–40°C to +100°C). External temperature sensor held constant.		0.005	0.008	°C/°C
Temperature monitor (TM) operational power supply current requirements (per temperature monitor instance, not including ADC or VAREFx)	VCC33A		200		µA
	VCC33AP		150		µA
	VCC15A		50		µA

Note: All results are based on averaging over 64 samples.

Embedded Design

Microsemi offers FREE SoftConsole Eclipse based IDE, which includes the GNU C/C++ compiler and GDB debugger. Microsemi also offers evaluation versions of software from Keil and IAR, with full versions available from respective suppliers.

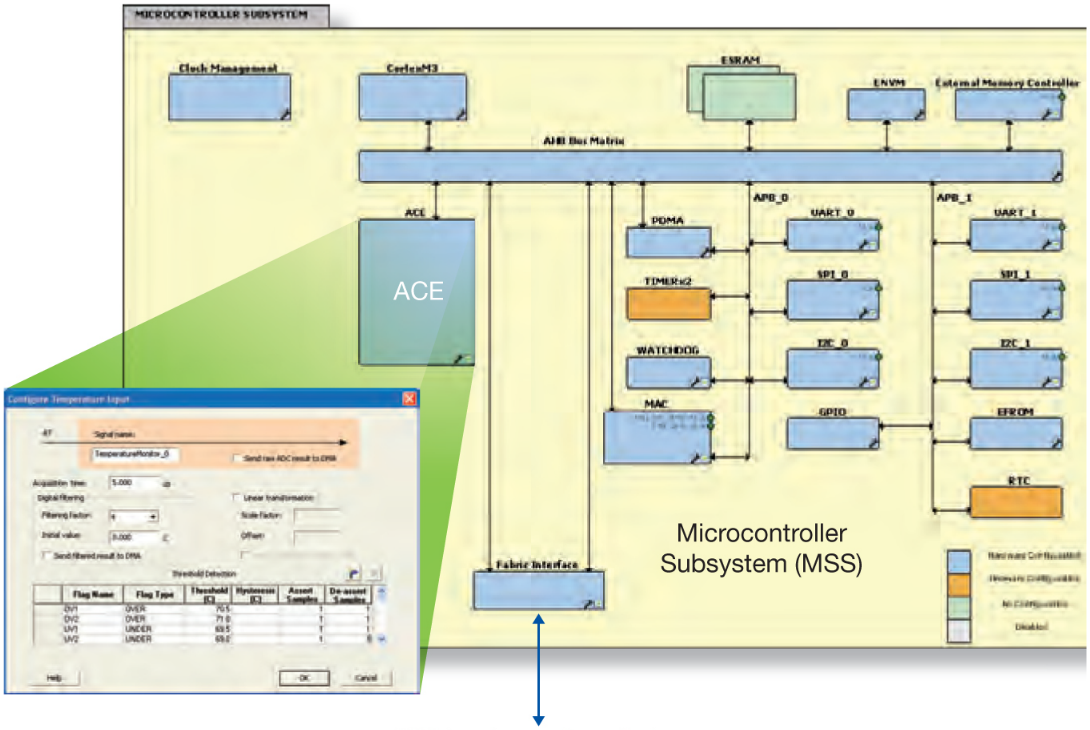
Analog Design

The MSS configurator provides graphical configuration for current, voltage and temperature monitors, sample sequencing setup and post-processing configuration, as well as DAC output.

The MSS configurator creates a bridge between the FPGA fabric and embedded designers so device configuration can be easily shared between multiple developers.

The MSS configurator includes the following:

- A simple configurator for the embedded designer to control the MSS peripherals and I/Os
- A method to import and view a hardware configuration from the FPGA flow into the embedded flow containing the memory map
- Automatic generation of drivers for any peripherals or soft IP used in the system configuration
- Comprehensive analog configuration for the programmable analog components
- Creation of a standard MSS block to be used in SmartDesign for connection of FPGA fabric designs and IP



Signal name: TemperatureMonitor_0

☐ Send raw ADC result to DMA

Acquisition time: 5.000 µs

Digital filtering

Filtering Factor: 4

Initial value: 0.000 C

☐ Send filtered result to DMA

☐ Linear transformation

Scale Factor:

Offset:

	Flag Name	Flag Type	Theshold (C)	Hysteresis (C)	Assert Samples	De-assert Samples
	OV1	OVER	70.5		1	1
	OV2	OVER	71.0		1	1
	UV1	UNDER	69.5		1	1
	UV2	UNDER	69.0		1	1

MSS Interface to SmartFusion
FPGA Fabric Blocks

Figure 3-2 • **MSS Configurator**

Emcraft Systems provides porting of the open-source U-boot firmware and uClinux™ kernel to the SmartFusion cSoC, a Linux®-based cross-development framework, and other complementary components. Combined with the release of its A2F-Linux Evaluation Kit, this provides a low-cost platform for evaluation and development of Linux (uClinux) on the Cortex-M3 CPU core of the Microsemi SmartFusion cSoC.

- Emcraft Linux on Microsemi's SmartFusion cSoC

Keil offers the RTX Real-Time Kernel as a royalty-free, deterministic RTOS designed for ARM and Cortex-M devices. It allows you to create programs that simultaneously perform multiple functions and helps to create applications which are better structured and more easily maintained.

- The RTX Real-Time Kernel is included with MDK-ARM. Download the Evaluation version of Keil MDK-ARM.
- RTX source code is available as part of Keil/ARM Real-Time Library (RL-ARM), a group of tightly-coupled libraries designed to solve the real-time and communication challenges of embedded systems based on ARM-powered microcontroller devices. The RL-ARM library now supports SmartFusion cSoCs and designers with additional key features listed in the "Middleware" section on page 3-5.

Micrium supports SmartFusion cSoCs with the company's flagship µC/OS family, recognized for a variety of features and benefits, including unparalleled reliability, performance, dependability, impeccable source code and vast documentation. Micrium supports the following products for SmartFusion cSoCs and continues to work with Microsemi on additional projects.

- SmartFusion Quickstart Guide for Micrium µC/OS-III Examples
  - Design Files

µC/OS-III™, Micrium's newest RTOS, is designed to save time on your next embedded project and puts greater control of the software in your hands.

RoweBots provides an ultra tiny Linux-compatible RTOS called Unison for SmartFusion. Unison consists of a set of modular software components, which, like Linux, are either free or commercially licensed. Unison offers POSIX® and Linux compatibility with hard real-time performance, complete I/O modules and an easily understood environment for device driver programming. Seamless integration with FPGA and analog features are fast and easy.

- Unison V4-based products include a free Unison V4 Linux and POSIX-compatible kernel with serial I/O, file system, six demonstration programs, upgraded documentation and source code for Unison V4, and free (for non-commercial use) Unison V4 TCP/IP server. Commercial license upgrade is available for Unison V4 TCP/IP server with three demonstration programs, DHCP client and source code.
- Unison V5-based products include commercial Unison V5 Linux- and POSIX-compatible kernel with serial I/O, file system, extensive feature set, full documentation, source code and more than 20 demonstration programs, Unison V5 TCP/IPv4 with extended feature set, sockets interface, multiple network interfaces, PPP support, DHCP client, documentation, source code and six demonstration programs, and multiple other features.

Middleware

Microsemi has ported both uIP and lwIP for Ethernet support as well as including TFTP file service.

- SmartFusion Webserver Demo Using uIP and FreeRTOS
- SmartFusion: Running Webserver, TFTP on lwIP TCP/IP Stack Application Note

The Keil/ARM Real-Time Library (RL-ARM)[1], in addition to RTX source, includes the following:

- RL-TCPnet (TCP/IP) – The Keil RL-TCPnet library, supporting full TCP/IP and UDP protocols, is a full networking suite specifically written for small ARM and Cortex-M processor-based microcontrollers. TCPnet is now ported to and supports SmartFusion Cortex-M3. It is highly optimized, has a small code footprint, and gives excellent performance, providing a wide range of application level protocols and examples such as FTP, SNMP, SOAP and AJAX. An HTTP server example of TCPnet working in a SmartFusion design is available.

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1. The CAN and USB functions within RL-ARM are not supported for SmartFusion cSoC.

Pin No.	FG256		
	A2F060 Function	A2F200 Function	A2F500 Function
D15	GCA1/IO20PDB0V0	IO24NDB1V0	IO33NDB1V0
D16	VCCFPGAIOB1	VCCFPGAIOB1	VCCFPGAIOB1
E1	EMC_DB[13]/IO44PDB5V0	EMC_DB[13]/GAC2/IO70PDB5V0	EMC_DB[13]/GAC2/IO87PDB5V0
E2	EMC_DB[12]/IO44NDB5V0	EMC_DB[12]/IO70NDB5V0	EMC_DB[12]/IO87NDB5V0
E3	GFA2/IO42PDB5V0	GFA2/IO68PDB5V0	GFA2/IO85PDB5V0
E4	EMC_DB[10]/IO43NPB5V0	EMC_DB[10]/IO69NPB5V0	EMC_DB[10]/IO86NPB5V0
E5	GNDQ	GNDQ	GNDQ
E6	GND	GND	GND
E7	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
E8	GND	GND	GND
E9	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
E10	GND	GND	GND
E11	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
E12	GCB2/IO22PDB1V0	GCA1/IO28PDB1V0	GCA1/IO36PDB1V0 *
E13	VCCFPGAIOB1	VCCFPGAIOB1	VCCFPGAIOB1
E14	GCA2/IO21PDB1V0	GCB1/IO27PDB1V0	GCB1/IO34PDB1V0
E15	GCC2/IO23PDB1V0	GDC1/IO29PDB1V0	GDC1/IO38PDB1V0
E16	IO23NDB1V0	GDC0/IO29NDB1V0	GDC0/IO38NDB1V0
F1	EMC_DB[9]/IO40PDB5V0	EMC_DB[9]/GEC1/IO63PDB5V0	EMC_DB[9]/GEC1/IO80PDB5V0
F2	GND	GND	GND
F3	GFB2/IO42NDB5V0	GFB2/IO68NDB5V0	GFB2/IO85NDB5V0
F4	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
F5	EMC_DB[11]/IO43PPB5V0	EMC_DB[11]/IO69PPB5V0	EMC_DB[11]/IO86PPB5V0
F6	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
F7	GND	GND	GND
F8	VCC	VCC	VCC
F9	GND	GND	GND
F10	VCC	VCC	VCC
F11	GND	GND	GND
F12	IO22NDB1V0	GCA0/IO28NDB1V0	GCA0/IO36NDB1V0 *
F13	NC	GNDQ	GNDQ

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin No.	FG256		
	A2F060 Function	**A2F200 Function**	**A2F500 Function**
T9	VAREF0	VAREF1	VAREF1
T10	ABPS0	ABPS6	ABPS6
T11	NC	ABPS5	ABPS5
T12	NC	SDD1	SDD1
T13	GNDVAREF	GNDVAREF	GNDVAREF
T14	GNDMAINXTAL	GNDMAINXTAL	GNDMAINXTAL
T15	VCCLPXTAL	VCCLPXTAL	VCCLPXTAL
T16	PU_N	PU_N	PU_N

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

6 – Datasheet Information

List of Changes

The following table shows important changes made in this document for each revision.

Revision	Changes	Page
Revision 13 (March 2015)	Updated Unused MSS I/O Configuration information in "User I/O Naming Conventions" (SAR 62994).	5-7
	Updated Table 2-90: "eNVM Block Timing, Worst Commercial Case Conditions: T_J = 85°C, VCC = 1.425 V". Changed the maximum clock frequency for the control logic – 5 cycles to 50 MHz for A2F060 and A2F200 devices (SAR 63920). Added the following Note: "Moving from 5:1:1:1 mode to 6:1:1:1 mode results in throughput change that is dependent on the system functionality. When the Cortex-M3 code is executed from eNVM - with sequential firmware (sequential address reads), the throughput reduction can be around 10%" (SAR 63920).	2-76
Revision 12 (November 2013)	CS288 package dimensions added to "SmartFusion cSoC Package Sizes Dimensions" table (SAR 43730).	1-III
	Added "Typical Programming and Erase Times" table (SAR 43732).	4-9
	Definition of Ethernet MAC clarified in the "General Description" section (SAR 50083).	1-1
	Clarified GC and GF global inputs in "Global I/O Naming Conventions" section and link to SF Fabric UG added (SAR 42802).	5-6
Revision 11 (September 2013)	Modified the description for VAREF0 in the "User-Defined Supply Pins"(SAR 30204).	5-5
	Updated the "Pin Assignment Tables" section with a note for A2F500, all packages with GCAx saying: "Signal assigned to those pins as a CLKBUF or CLKBUF_LVPECL or CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal (SAR 45985).	5-18